

PATENT APPLICATION
042390.P10047C

Amendments to the Specification

After the title, please insert the following as the first sentence of the specification:

"This is a continuation of application No. 09/897,174, filed June 29, 2001."

Please replace the paragraph that begins on page 4, line 7, and ends on page 4 line 17, of the Application with the following amended paragraph:

Figure 1 is an elevational cross-section illustration of a memory structure 10 during fabrication of a ferroelectric polymer (FEP) memory according to one embodiment. A substrate 12 is depicted as being patterned with a mask 14 and a recess 16 has been formed in substrate 12 through mask 14. Recess 16 is prepared to accept a first or lower electrode 18 as depicted in Figure 2. First electrode 18 may be formed by chemical vapor deposition (CVD) of any material that is suitable as an electrical conductor according to electrical conductors known in the art. In one embodiment, first electrode 18 is an aluminum material. In one embodiment, first electrode 18 is a copper or copper alloy material or other non-transparent electrode material. The thickness of the first electrode 18 (and the second electrode 34, depicted in Figure 5) may depend upon the specific lithography and design rules. Figure 2 also illustrates extraneous electrode material 18' above and on mask 14, both of which will be removed.

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Please replace the paragraph that begins on page 9, line 21, and ends on page 10 line 5, of the Application with the following amended paragraph:

Figure 5 also illustrates further processing in which a second or upper protective film 32 and a second or upper electrode 34 are formed in a configuration that may be referred to as a "cross point" 36 array that exposes FEP structure 38 between first electrode 18 and second electrode 34. In other words, the cross point 36 or projection of the width W, of first electrode 18 upward onto second electrode 34 exposes an area of FEP structure 38 that is about equivalent to the square of width W if second electrode 34 also has a width of about width W. The amount of FEP structure 38 that is within this projected area may be most susceptible of being written to and read from as a memory element embodiment. In one embodiment, second electrode 34 is aluminum or copper material and may be a non-transparent electrode. In the embodiment wherein first electrode 18 and second electrode 34 are non-transparent electrodes, memory structure 10 may be a non-optical memory or non-optical storage device.